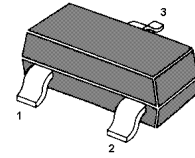


MMBT A55

PNP General Purpose Transistor for amplifier applications

On special request, these transistors can be manufactured in different pin configurations.

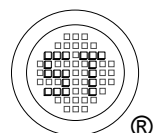


1. Base 2. Emitter 3. Collector

TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	60	V
Emitter Base Voltage	$-V_{EBO}$	4	V
Collector Current	$-I_C$	500	mA
Power Dissipation	P_{tot}	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_j	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 to +150	$^\circ\text{C}$



MMBT A55

Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-I_C = 10\text{ mA}$, $-V_{CE} = 1\text{ V}$ at $-I_C = 100\text{ mA}$, $-V_{CE} = 1\text{ V}$	h_{FE} h_{FE}	100 100	- -	- -
Collector Cutoff Current at $-V_{CB} = 60\text{ V}$	$-I_{CBO}$	-	100	nA
Collector Cutoff Current at $-V_{CE} = 60\text{ V}$	$-I_{CES}$	-	100	nA
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	60	-	V
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	4	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	0.25	V
Base Emitter On Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$,	$-V_{BE(on)}$	-	1.2	V
Gain Bandwidth Product at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$, $f = 100\text{ MHz}$	f_T	50	-	MHz

